



STP/F21NM50N - STW21NM50N STB21NM50N - STB21NM50N-1

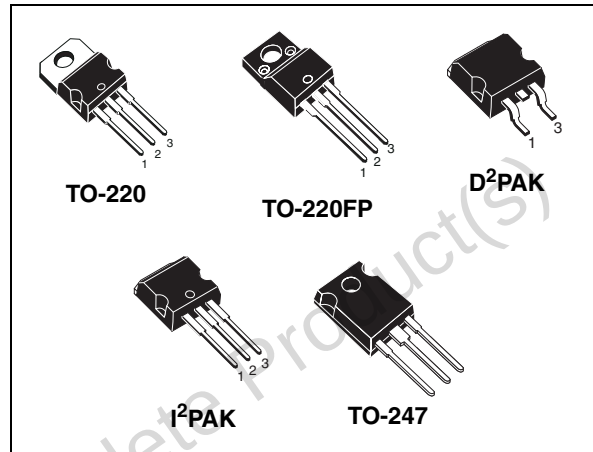
N-channel 500V - 0.15Ω - 18A TO-220/FP/D²/I²PAK/TO-247
Second generation MDmesh™ Power MOSFET

General features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)}	I _D
STB21NM50N	550V	< 0.19Ω	18A
STB21NM50N-1	550V	< 0.19Ω	18A
STF21NM50N	550V	< 0.19Ω	18A ⁽¹⁾
STP21NM50N	550V	< 0.19Ω	18A
STW21NM50N	550V	< 0.19Ω	18A

1. Limited by wire bonding

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



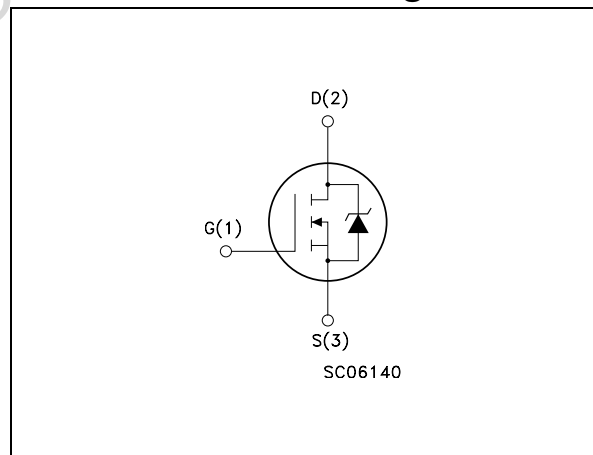
Description

The devices are realized with the second generation of MDmesh Technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters

Applications

- Switching application

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STB21NM50N	B21NM50N	D ² PAK	Tape & reel
STB21NM50N-1	B21NM50N	I ² PAK	Tube
STF21NM50N	F21NM50N	TO-220FP	Tube
STP21NM50N	P21NM50N	TO-220	Tube
STW21NM50N	W21NM50N	TO-247	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/ D ² PAK/ I ² PAK/TO-247	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	500		V
V _{GS}	Gate- source voltage	±25		V
I _D	Drain current (continuous) at T _C = 25°C	18	18 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100°C	11	11 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	72	72 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25°C	140	30	W
	Derating factor	1.12	0.23	W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
Viso	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T _C =25°C)	--	2500	V
T _{stg}	Storage temperature	-55 to 150		°C
T _j	Max. operating junction temperature	150		

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 18 A, di/dt ≤ 400 A/μs, V_{DD} = 80% V_{(BR)DSS}

Table 2. Thermal data

Symbol	Parameter	TO-220/D ² PAK/ I ² PAK / TO-247	TO-220FP	Unit
R _{thj-case}	Thermal resistance junction-case max	0.89	4.21	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	62.5		°C/W
T _l	Maximum lead temperature for soldering purpose	300		°C

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	9	A
E _{AS}	Single pulse avalanche energy (starting T _j = 25°C, I _D = I _{AR} , V _{DD} = 50V)	480	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	500			V
$dv/dt^{(1)}$	Drain source voltage slope	$V_{DD}=400\text{V}$, $I_D=25\text{A}$, $V_{GS}=10\text{V}$	44			V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C @ 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 9\text{A}$		0.150	0.190	Ω

1. Characteristic value at turn off on inductive load

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$, $I_D = 9\text{A}$		12		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$		1950 420 60		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 400\text{V}$		270		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 250\text{V}$, $I_D = 9\text{A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{V}$ (see Figure 15.)		22 18 90 30		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 400\text{V}$, $I_D = 18\text{A}$, $V_{GS} = 10\text{V}$, (see Figure 16.)		65 10 30		nC nC nC
R_g	Gate input resistance	$f=1\text{MHz}$ Gate DC Bias=0 test signal level=20mV open drain		1.6		Ω

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				72	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 18A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 18A,$ $di/dt=100A/\mu s$ $V_{DD} = 100V,$ (see Figure 17.)		360		ns
Q_{rr}	Reverse recovery charge			5		μC
I_{RRM}	Reverse recovery current			27		A
t_{rr}	Reverse recovery time	$I_{SD} = 18A,$ $di/dt=100A/\mu s$ $V_{DD} = 100V, T_j = 150^\circ C$ (see Figure 17.)		464		ns
Q_{rr}	Reverse recovery charge			6.5		μC
I_{RRM}	Reverse recovery current			27		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

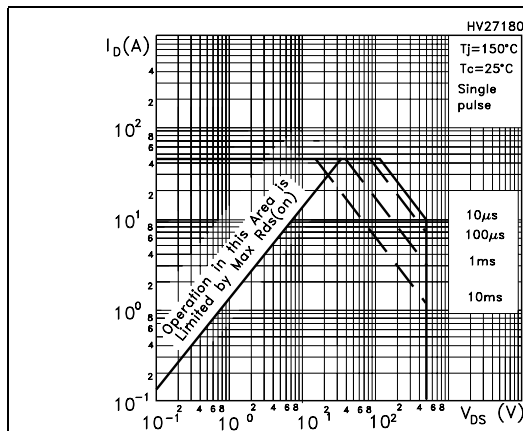


Figure 2. Thermal impedance

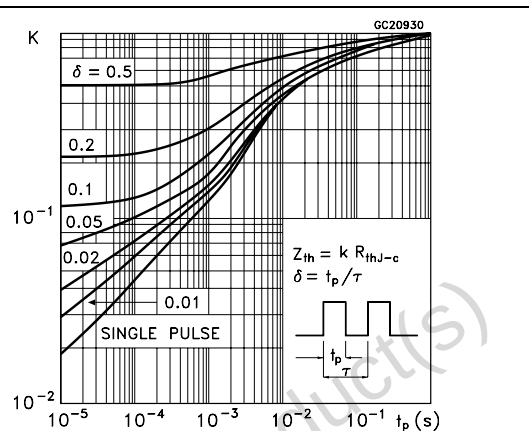


Figure 3. Safe operating area for TO-220FP

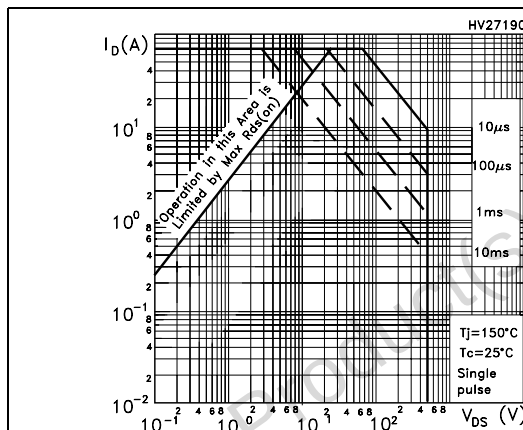


Figure 4. Thermal impedance for TO-220FP

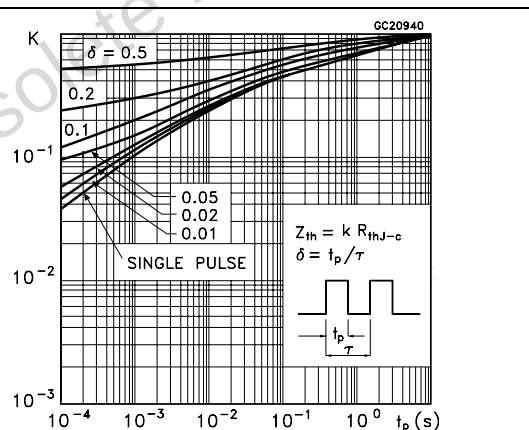


Figure 5. Output characteristics

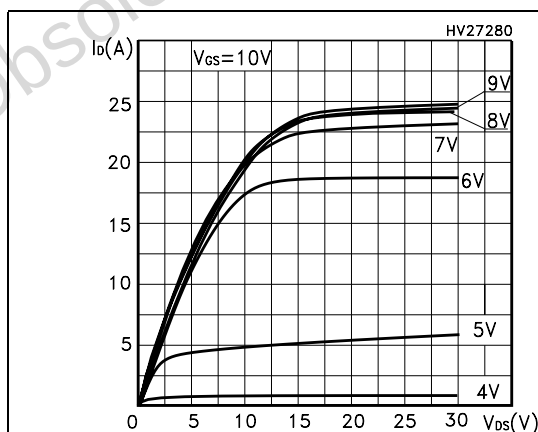


Figure 6. Transfer characteristics

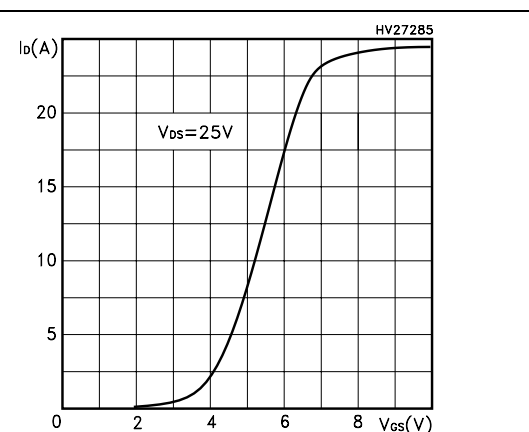


Figure 7. Transconductance

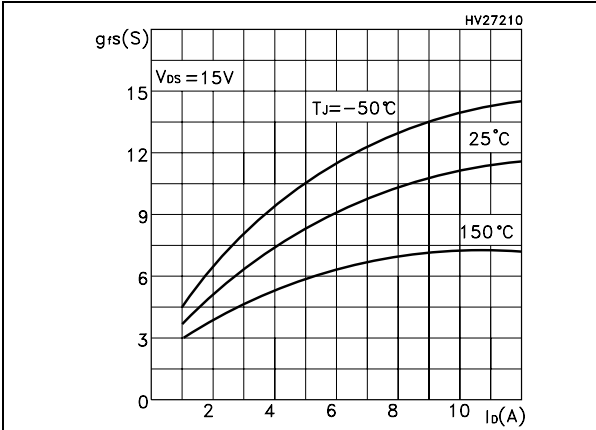


Figure 8. Static drain-source on resistance

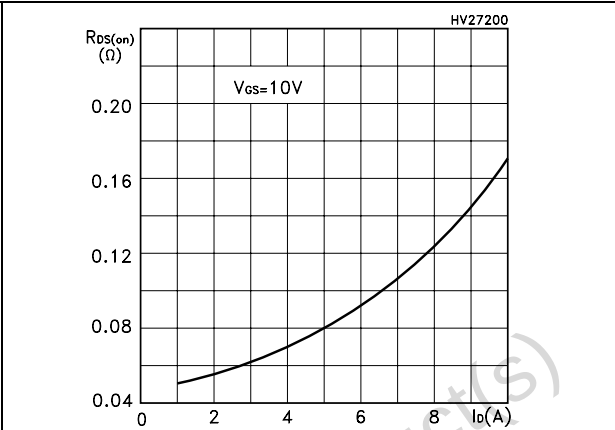


Figure 9. Gate charge vs gate-source voltage

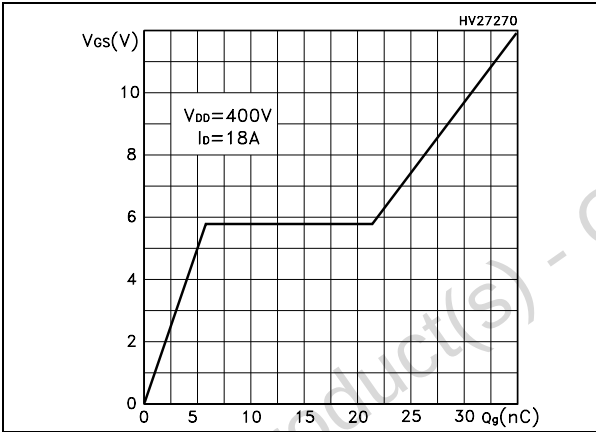


Figure 10. Capacitance variations

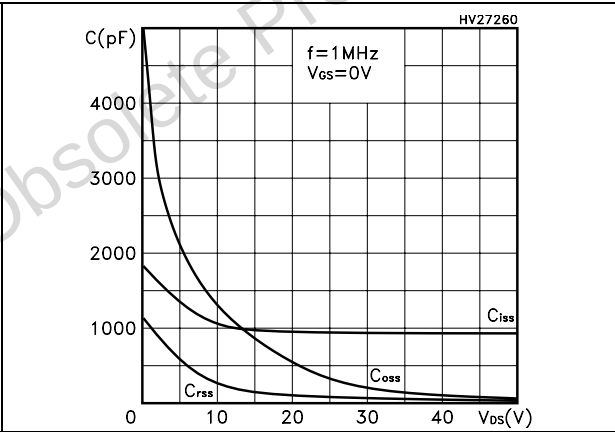


Figure 11. Normalized gate threshold voltage vs temperature

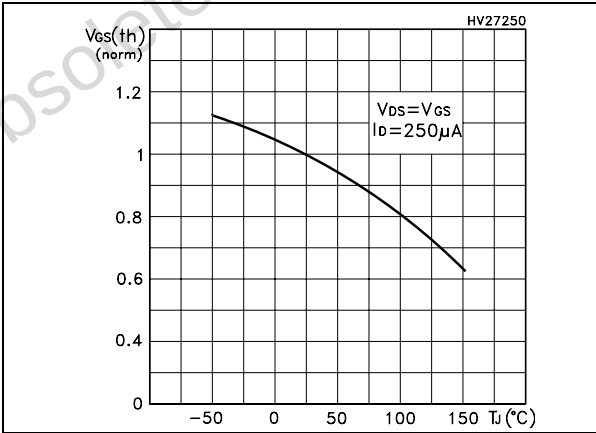


Figure 12. Normalized on resistance vs temperature

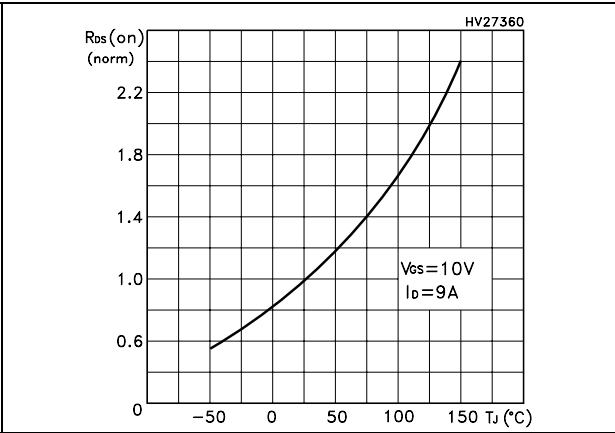


Figure 13. Source-drain diode forward characteristics

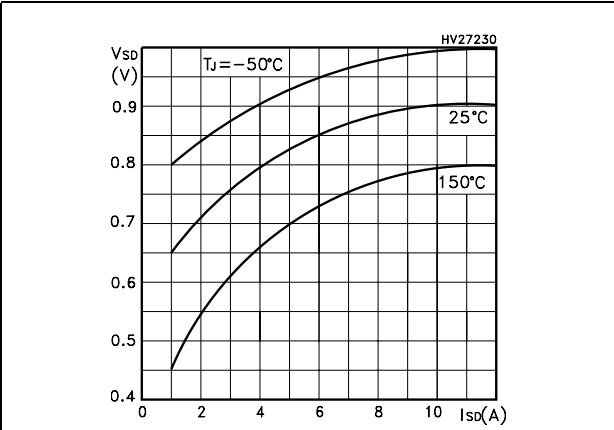
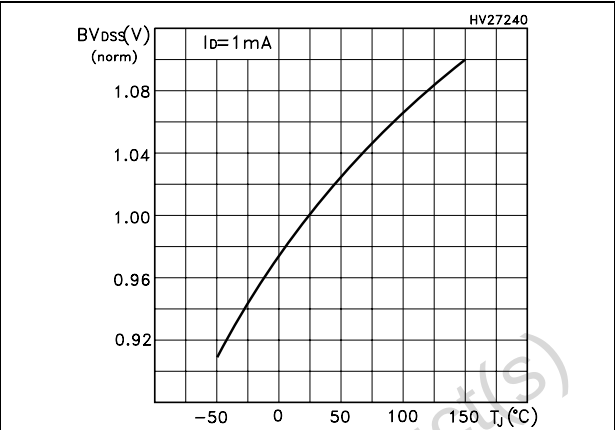


Figure 14. Normalized BV_{DSS} vs temperature



3 Test circuit

Figure 15. Switching times test circuit for resistive load

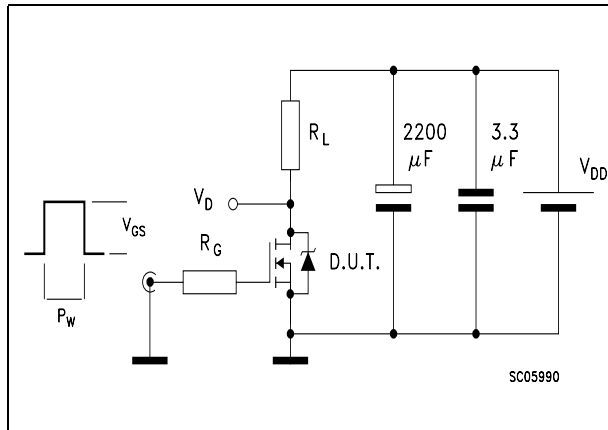


Figure 16. Gate charge test circuit

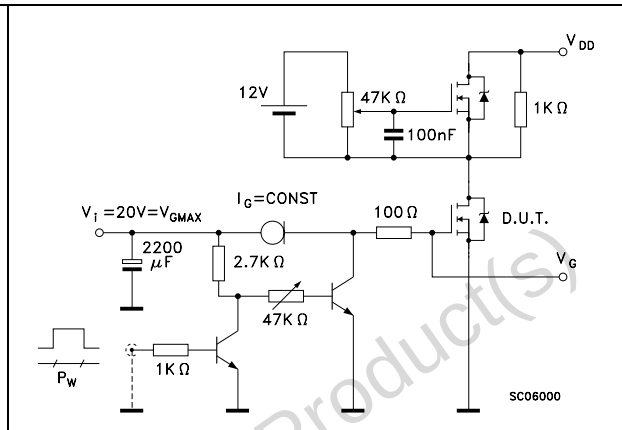


Figure 17. Test circuit for inductive load switching and diode recovery times

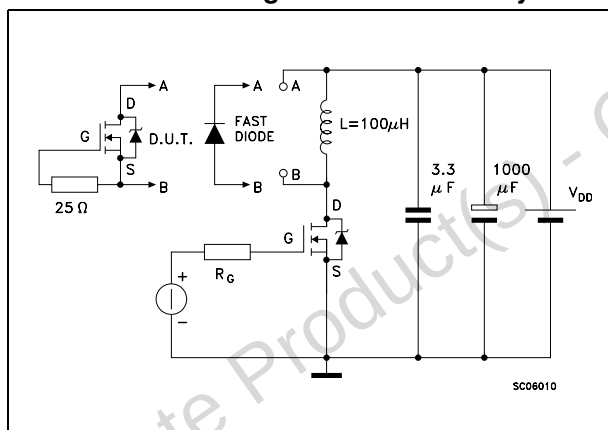


Figure 18. Unclamped Inductive load test circuit

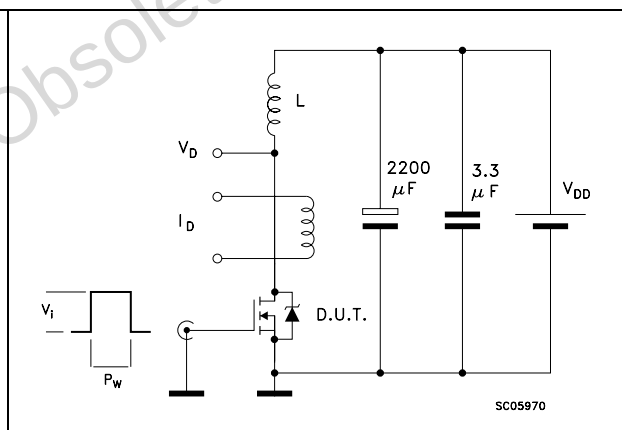


Figure 19. Unclamped inductive waveform

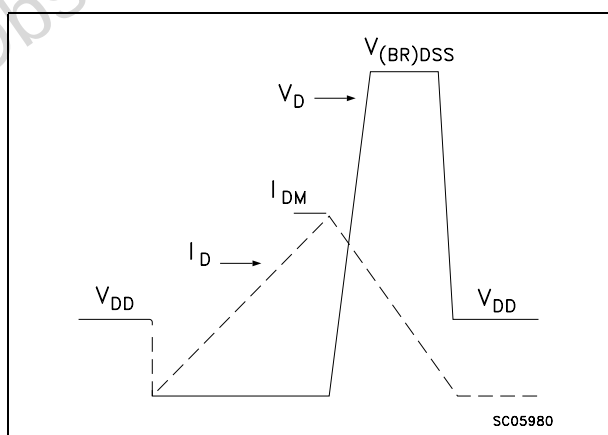
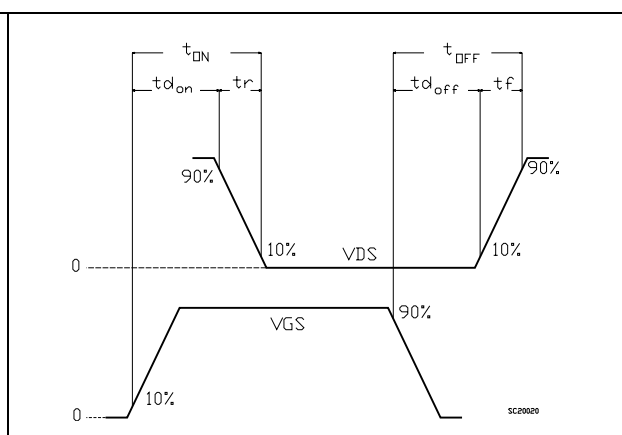


Figure 20. Switching time waveform



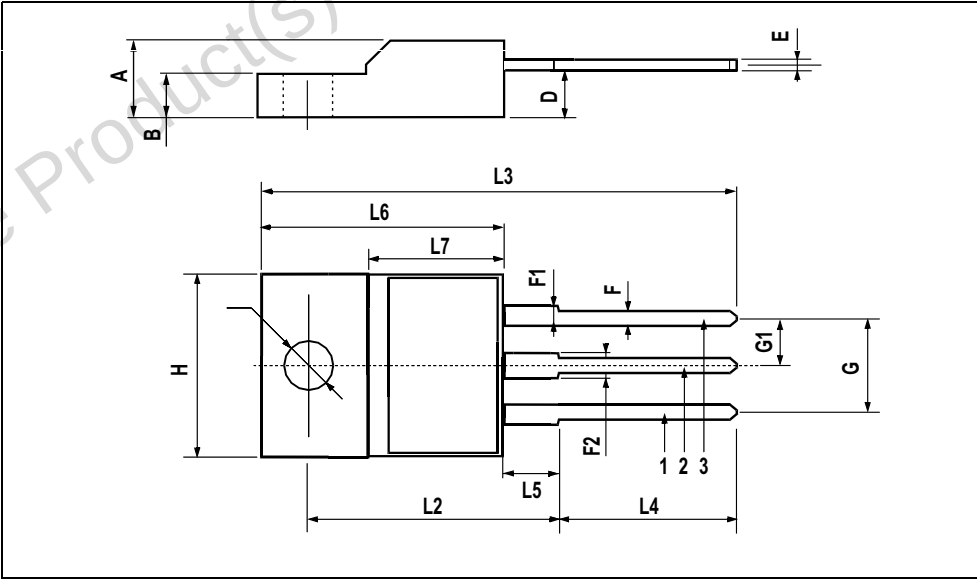
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s) - Obsolete Product(s)

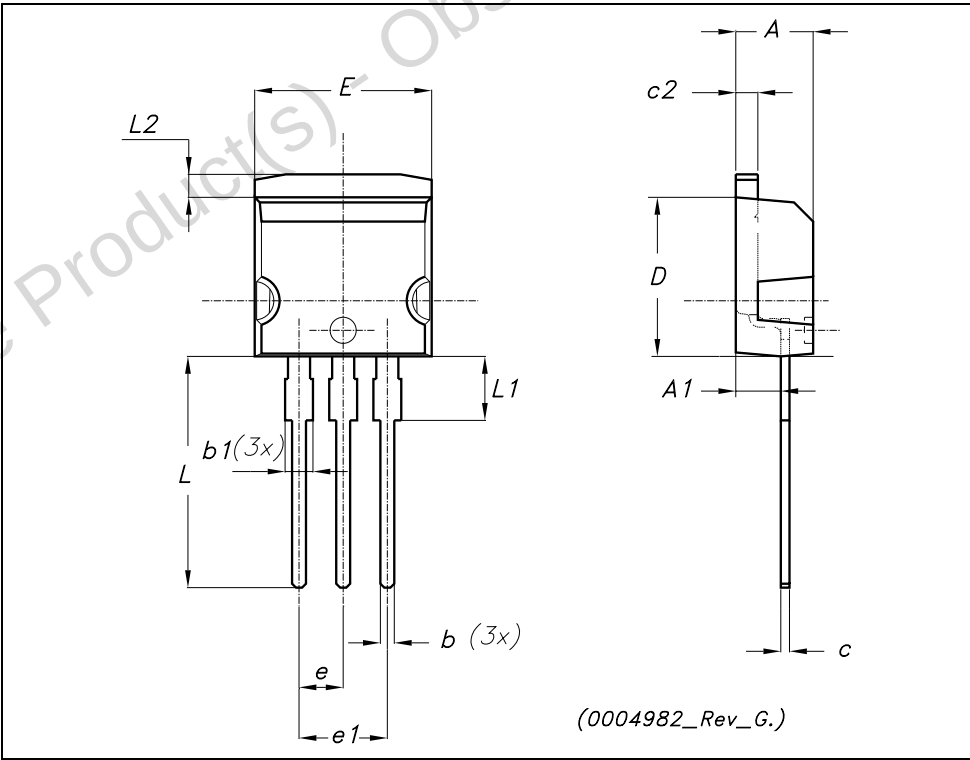
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



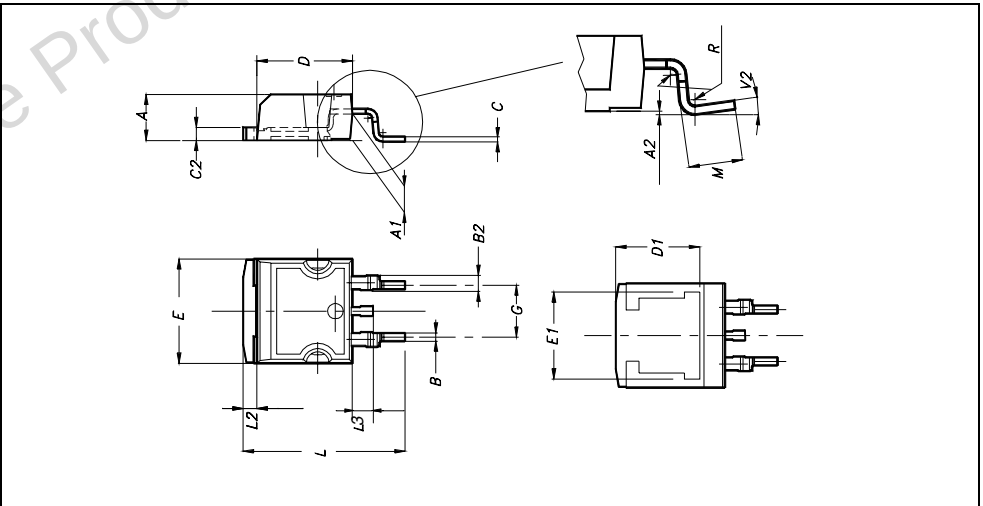
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



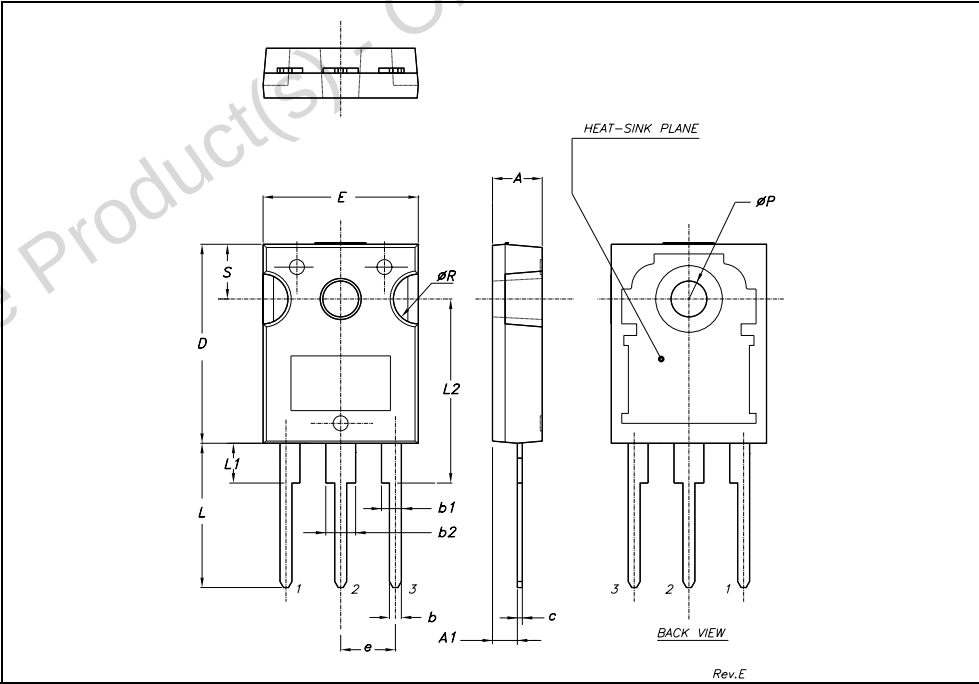
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



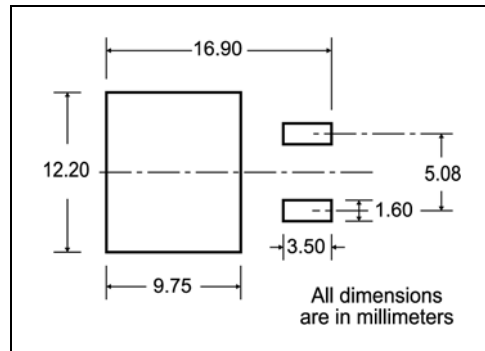
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	

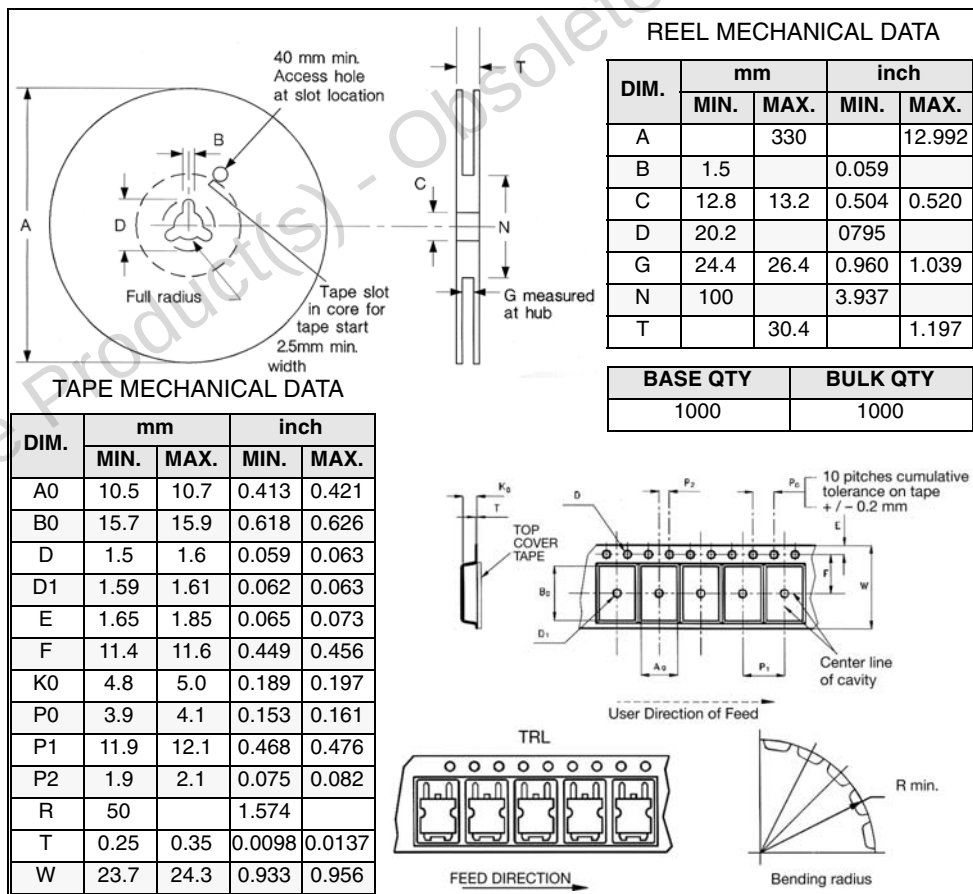


5 Packing mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
29-Sep-2005	1	First release
05-Oct-2005	2	Symbol changed on Dynamic
19-Oct-2005	3	Changed Figure 8: Static drain-source on resistance
29-Nov-2005	4	Modified Figure 5: Output characteristics
20-Nov-2006	5	Modified Figure 8: Static drain-source on resistance
19-Jan-2007	6	Typo mistake on Table 5 .

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